

Supporting Information for

Hybrid Field-Effect Transistors and Photodetectors Based on Organic Semiconductor and CsPbI₃ Perovskite Nanorods Bilayer Structure

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Supplementary Figures

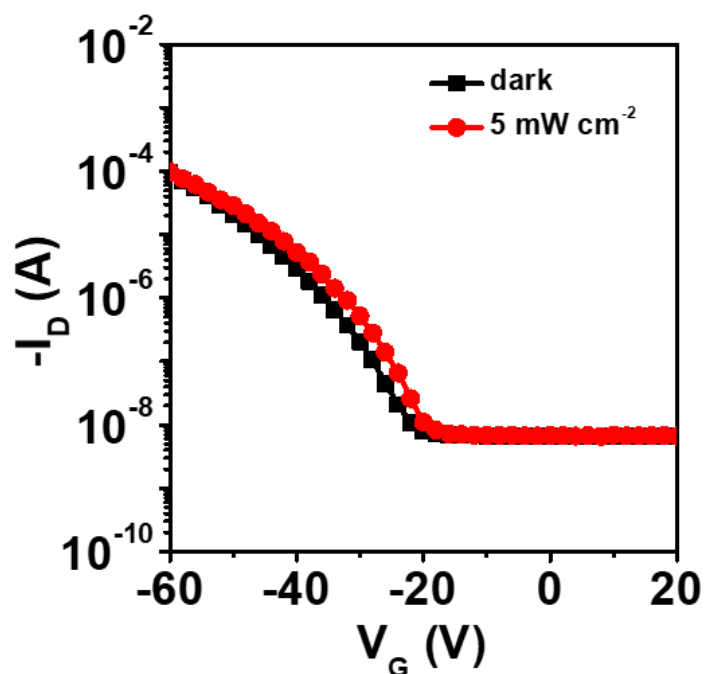


Fig. S1 Photoresponse properties for transistors based on C8BTBT in the dark and under light illumination (10 mW cm^{-2}) at $V_D = -30 \text{ V}$

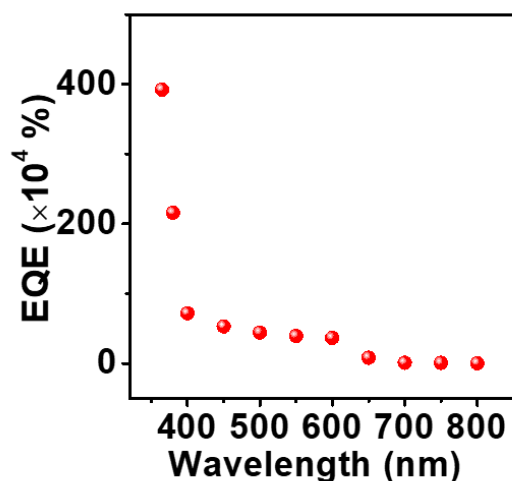


Fig. S2 Calculated EQE of the hybrid phototransistors as a function of the illumination wavelength under 0.5 mW cm^{-2} at $V_G = -60 \text{ V}$, $V_D = -30 \text{ V}$

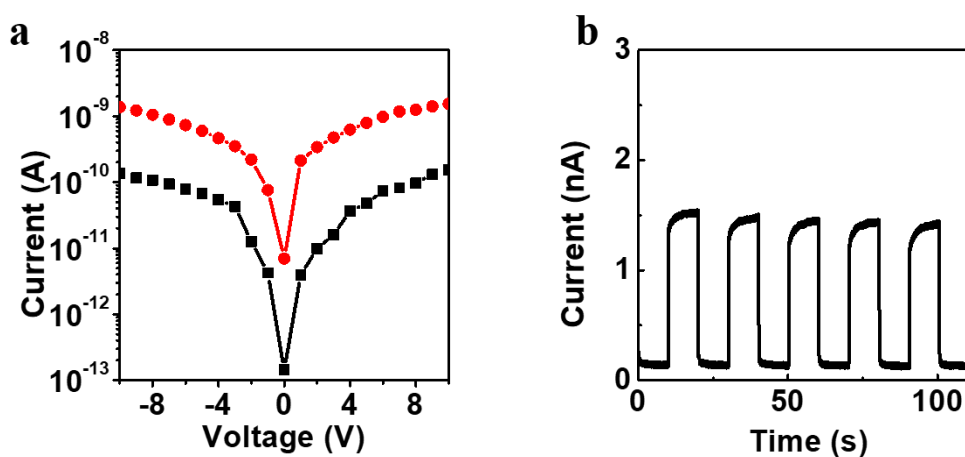


Fig. S3 **a** I - V curves of the only CsPbI₃ nanorods-based photodetectors measured in dark and under 5 mW cm^{-2} . **b** Time-dependent photoresponse of the only CsPbI₃ nanorods-based photodetectors measured in dark and under 5 mW cm^{-2} at 10 V

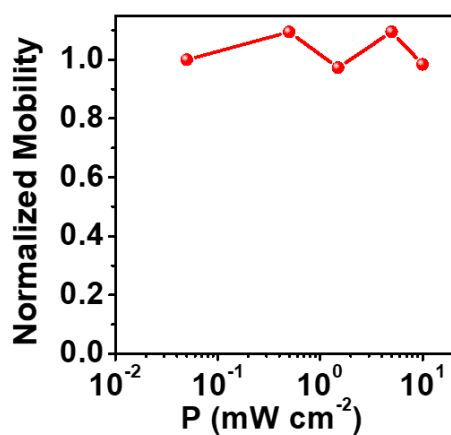


Fig. S4 Normalized mobility of the hybrid phototransistors versus the power intensity at $V_D = -30 \text{ V}$

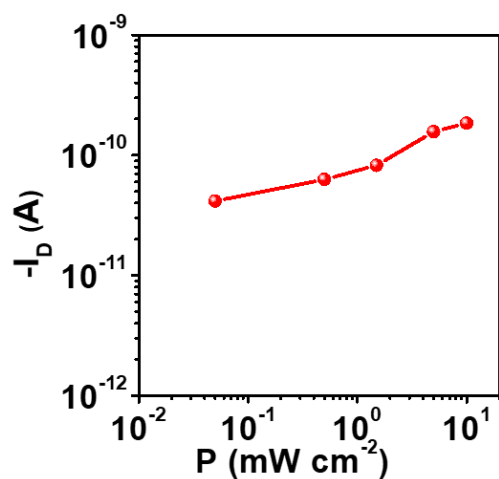


Fig. S5 The output current in off-state of the hybrid phototransistor as a function of the power intensity at $V_D = -30$ V

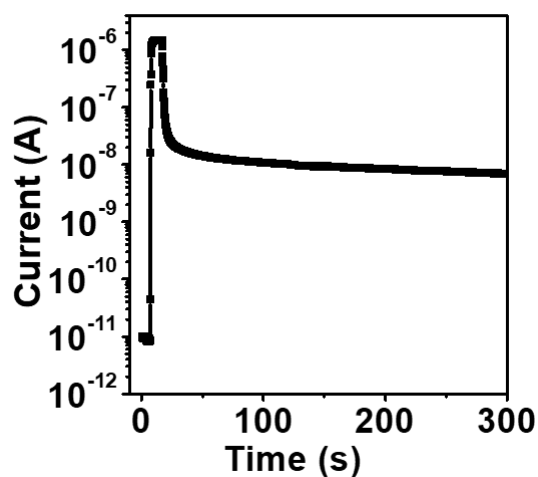


Fig. S6 10 s white light irradiation of the hybrid devices under 0.5 mW cm^{-2} followed by removal of light incident to allow relaxation for 5 min

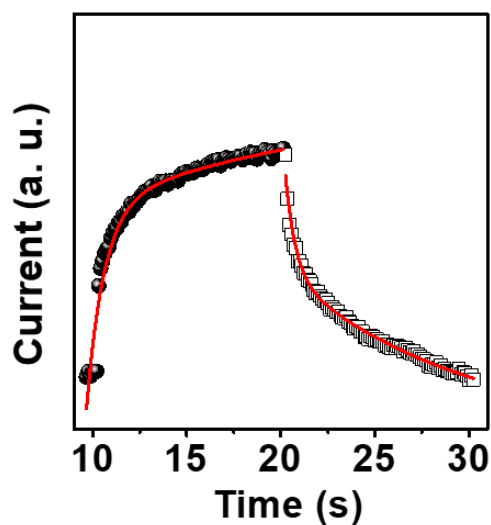


Fig. S7 The photoresponse curves of the hybrid phototransistor and the fitted lines

Table S1 Performance comparison of our C8BTBT/CsPbI₃ nanorods-based photodetectors with low-dimensional all inorganic perovskite-based photodetectors in literatures

Material	Light source	R(A W ⁻¹)	I _{photo} /I _{dark}	Stability	Ref.
CsPbI ₃ nanorods	405 nm	2.92 × 10 ³	3 × 10 ³	1 week	[1]
CsPbI ₃ nanoarrays	N/A	0.0067	N/A	N/A	[2]
CsPbI ₃ nanowires	White light	N/A	100	4 weeks	[3]
CsPbI ₃ nanocrystals	405 nm	N/A	10 ⁵	N/A	[4]
films					
CsPbI ₃ QDs	525 nm	1.5	10 ⁴	60 days	[5]
/NaYF ₄ :Yb,Er QDs					
CsPb(Br/I) ₃ nanorods	532 nm	N/A	10 ³	N/A	[6]
CsPbI₃ nanorods	White light	5.3 × 10³	2.2 × 10⁶	1 month	This work
/C8BTBT					

Supplementary References

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